PATENT ABSTRACTS OF JAPAN

(11)Publication number:

10-163307

(43)Date of publication of application: 19.06.1998

(51)Int.CI.

H01L 21/68 H01L 21/3065

HO2N 13/00

(21)Application number: 08-323679

(71)Applicant :

SONY CORP

(22)Date of filing:

04.12.1996

(72)Inventor:

KADOMURA SHINGO

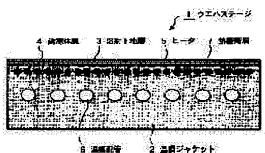
SHIROSAKI TOMOHIDE HIRANO SHINSUKE TAKATSU MEGUMI

(54) WAFER STAGE AND MANUFACTURE THEREOF AND DRY-ETCHING APPARATUS

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a wafer stage for enabling high temperature heating of a wafer by providing an electrostatic chuck and by eliminating the trouble upon high temperature heating

SOLUTION: In case where a water stage 1 is constructed so that it gives an electrostatic chuck function to a temperature control jacket 2, the temperature control jacket 2 is made of aluminum or aluminum alloy within which a heater 5 and a thermal medium pipe 6 connected to temperature control means are buried and a thermal buffer layer 7 is integrally provided on the upper surface thereof. The thermal buffer layer 7 is formed by making aluminum or aluminum alloy flow into the holes of a porous Al2O3 plat—shaped member and by compounding them. A dielectric film 4 consisting of an insulating material is formed on the thermal buffer layer 7 of the temperature control jacket 2 through a fusion—jet process. The temperature conditioning jacket 2 and the dielectric film 4 perform the function as the electrostatic chuck because the temperature control jacket 2 is used as an electrode.



LEGAL STATUS

[Date of request for examination]

18.05.2001

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

3438496

[Date of registration]

13,06,2003

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office